
Oral presentation | 13 Semiconductors | 13.7 Compound and power electron devices and process technology

[19p-CE-5~17]13.7 Compound and power electron devices and process technology

Masashi Kato(NITech), Taketomo Sato(Hokkaido Univ.)

Wed. Sep 19, 2018 3:00 PM - 6:45 PM CE (Century Hall)

△ : Presentation by Applicant for JSAP Young Scientists Presentation Award

▲ : English Presentation

▼ : Both of Above

No Mark : None of Above

3:00 PM - 3:30 PM

[19p-CE-5][JSAP Paper Award Speech] Hydride-vapor-phase epitaxial growth of highly pure GaN layers with smooth as-grown surfaces on freestanding GaN substrates

OHajime Fujikura¹, Taichiro Konno¹, Takehiro Yoshida¹, Fumimasa Horikiri¹ (1.SCIOCS)

Keywords:JSAP Paper Award